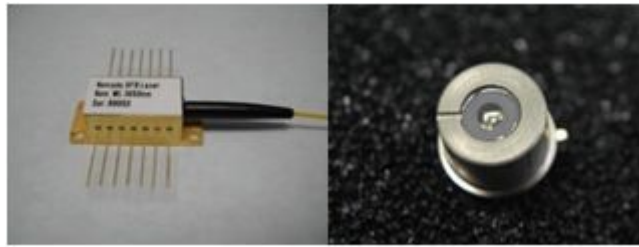


DFB-0785-100-T03, DFB Diode Laser

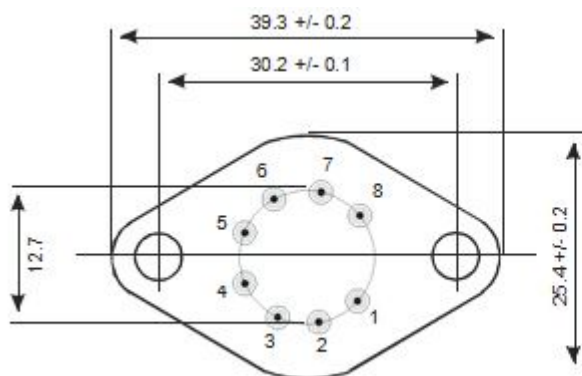


Wavelength: Selection for Raman Spectroscopy 785nm
 The DFB-0785-100-T03 is a high power MOVPE grown GaAsP/AlGaAs Distributed Feedback diode laser. The chips are mounted in TO3 can with Peltier cooler. Fully mode-hop free tuning selection available upon request.

Specification(The characteristics are measured at 25°C operation temperature.)

Parameter	Symbol	Unit	min.	typ.	max.
Center Wavelength	c	nm	784	785	786
Spectral Width		MHz		2	10
Temperature Coefficient	T	nm/K		0.06	
Laser Current Coefficient	I	nm/mA		0.003	
Output Power	P _{opt}	mW	100		
Slope Efficiency		mW/mA	0.6	0.8	1.0
Threshold Current	I _{th}	mA			70
Operation Current @ P _{opt} = 80mW	I _{opt}	mA			180
Beam Divergence (FWHM)		deg.	6	8	10
Beam Divergence (FWHM)		deg.	18	21	24
Polarization				TM	
Mode Structure			fundamental transverse mode		

Laser Mount: T03 - can with Peltier cooler



- Pin 1: TEC (+)
- Pin 2: NTC Thermistor 10kΩ at 25°C
- Pin 3: NTC Thermistor 10kΩ at 25°C
- Pin 4: Laser Cathode (-)
- Pin 5: Laser Anode (+)
- Pin 6: Photodiode Anode (+)
- Pin 7: Photodiode Cathode (-)
- Pin 8: TEC (-)